

Serial No.: 10/003,287  
Atty. Docket No.: P67237US0

**IN THE ABSTRACT:**

Please amend the abstract as follows:

--ABSTRACT

A method of fabricating an exposure mask ~~for semiconductor manufacture to~~  
~~improve the accuracy of critical dimensions of the mask pattern. The method includes~~ including the  
steps of forming a chrome layer, a first photo resist, an Ag layer as a conductive layer and a second  
photo resist on a transparent quartz substrate, in sequence; forming and using a second photo resist  
pattern ~~by exposing and developing the second photo resist; forming to form~~ a conductive layer  
pattern by etching the conductive layer ~~using the second photo resist pattern as an etch barrier;~~  
removing the second photo resist pattern; forming an oxide layer ~~as a layer~~ for shielding light at the  
surface of the conductive layer pattern and ~~by oxidizing the conductive layer pattern;~~ exposing the  
first photo resist using the conductive layer pattern with ~~having~~ the oxide layer thereon ~~at the~~  
~~surface thereof;~~ forming a first photo resist pattern exposing the chrome layer and ~~by developing the~~  
~~exposed first photo resist;~~ forming a mask pattern including the chrome layer by selectively etching  
the exposed chrome layer ~~parts;~~ and removing the conductive layer pattern including the oxide layer  
and the first photo resist pattern.--